JJMICROELECTRONICS

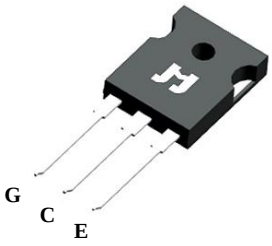
1200V 40A Trench and Field Stop IGBT

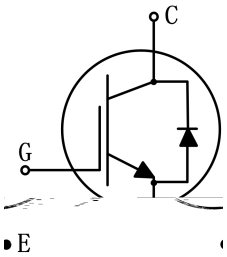
JJT40N120HK

Key performance:

- V_{CE} =1200V
- I_C=40A@T_C=100
- $V_{CE(sat)}$=1.9V

TO-247





Features:

- Trench and field-stop technology
- High speed switching
- Low collector to emitter saturation voltage
- Easy parallel switching capability
- High ruggedness performance
- RoHS compliant

Applications:

- Welding machines
- UPS
- Solar inverters

Package parameters

Type	Marking	Package	Packaging Method
JJT40N120HK	T40120HK	TO-247	Tube

Symbol	Parameter	Values	Unit
V_{CES}	Collector-emitter voltage	1200	V
V_{GES}	Gate-emitter voltage	±20	V
I_C	Continuous collector current (T_C=25)	80	A
	Continuous collector current (T_C=100)	40	A
I_{CM}	Pulsed collector current, t_p limited by T_{vjmax}	160	A
I_F	Diode continuous forward current (T_C=100)	40	A
I_{FM}	Diode maximum current, t_p limited by T_{vjmax}	160	A
P_{tot}	Power dissipation (T_C=25)	250	W
	Power dissipation (T_C=100)	125	W
T_{vj}	Operating junction temperature range	-40 to +175	
T_{stg}	Storage temperature range	-55 to +150	

Symbol	Parameter	Values		Unit
		Typ.	Max.	
$R_{th(j-c)}$	Thermal resistance, junction to case for IGBT			

Electrical characteristics of IGBT (T_{vj}=25 unless otherwise specified)

Static characteristics

Symbol	Parameter	Test condition	Values			Unit
			Min.	Typ.	Max.	
BV_{CES}	Collector-emitter breakdown voltage	V_{GE}=0V, I_C=250μA	1200	-	-	V
I_{CES}	Collector-emitter leakage current	V_{CE}=1200V, V_{GE}=0V	-	-	100	μA
I_{GES}	Gate leakage current, forward	V_{GE}=20V, V_{CE}=0V	-	-	100	nA
	Gate leakage current, reverse	V_{GE}=-20V, V_{CE}=0V	-	-	-100	nA
$V_{GE(th)}$	Gate-emitter threshold voltage	V_{GE}=V_{CE}, I_C=1mA	5.0	6.0	7.0	V
$V_{CE(sat)}$	Collector-emitter saturation voltage	V_{GE}=15 V, I_C=40A	-	1.9	-	V
		V_{GE}=15V, I_C=40A, T_{vj}=175	-	2.2	-	V

Dynamic characteristics

Symbol	Parameter	Test condition	Values			Unit
			Min.	Typ.	Max.	
C_{ies}	Input capacitance	V_{CE}=30V V_{GE}=0V f=1MHz	-	9900	-	pF
C_{oes}	Output capacitance		-	189	-	pF
C_{res}	Reverse transfer capacitance		-	40	-	pF
Q_g	Total gate charge	V_{CC}=960V V_{GE}=15V I_C=40A	-	263	-	nC

Switching characteristics

Symbol	Parameter	Test condition	Values			Unit
			Min.	Typ.	Max.	
$t_{d(on)}$	Turn-on delay time	V_{CC}=600V V_{GE}=0/15V I_C=40A R_G=10Ω Inductive load	-	85	-	ns
t_r	Rise time		-	76	-	ns
$t_{d(off)}$	Turn-off delay time		-	307	-	ns
t_f	Fall time		-	69	-	ns
E_{on}	Turn-on energy		-	2.5	-	mJ
E_{off}	Turn-off energy		-	1.4	-	mJ
E_{ts}	Total switching energy		-	3.9	-	mJ
$t_{d(on)}$	Turn-on delay time	V_{CC}=600V V_{GE}=0/15V I_C=40A R_G=10Ω Inductive load T_{vj}=175	-	76	-	ns
t_r	Rise time		-	75	-	ns
$t_{d(off)}$	Turn-off delay time		-	360	-	ns
t_f	Fall time		-	149	-	ns
E_{on}	Turn-on energy		-	2.9	-	mJ
E_{off}	Turn-off energy		-	2.6	-	mJ
E_{ts}	Total switching energy		-	5.5	-	mJ

Electrical characteristics of Diode (T_{vj}=25 unless otherwise specified)

Symbol	Parameter	Test condition	Values			Unit
			Min.	Typ.	Max.	
V_F	Diode forward voltage	I_F=40A	-	2.0	-	V
		I_F=40A T_{vj}=175	-	1.6	-	V
t_{rr}	Diode reverse recovery time	V_R=600V I_F=40A di_F/dt=-750A/μs	-	175	-	ns
I_{rrm}	Diode peak reverse recovery current		-	24	-	A
Q_{rr}	Diode reverse recovery charge		-	2000	-	nC
t_{rr}	Diode reverse recovery time	V_R=600V I_F=40A di_F/dt=-750A/μs T_{vj}=175	-	285	-	ns
I_{rrm}	Diode peak reverse recovery current		-	37	-	A
Q_{rr}	Diode reverse recovery charge		-	5500	-	nC

Typical performance characteristics

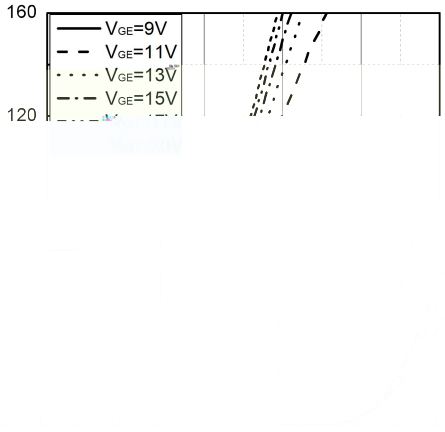


Fig 1. Typical output characteristic (T_{vj}=25)

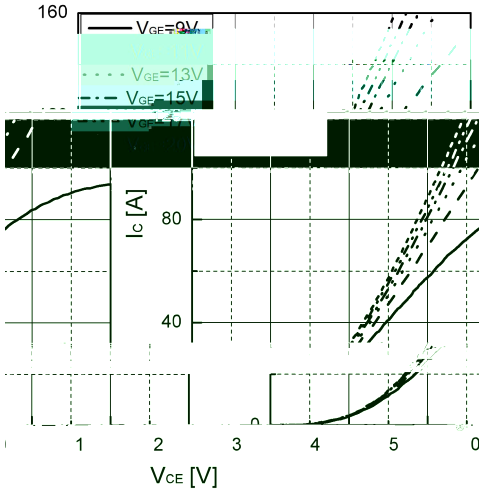


Fig 2. Typical output characteristic(T_{vj}=175)

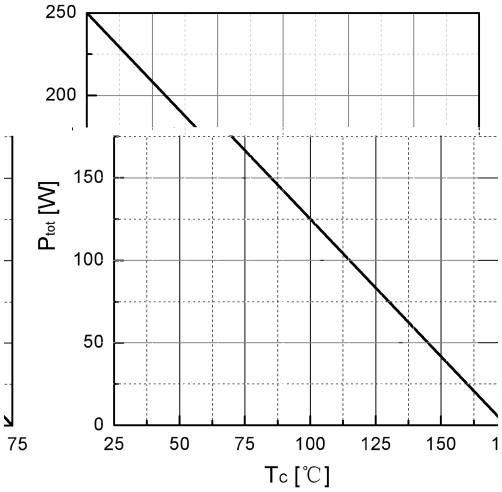


Fig 3. Power dissipation as a function of T_C

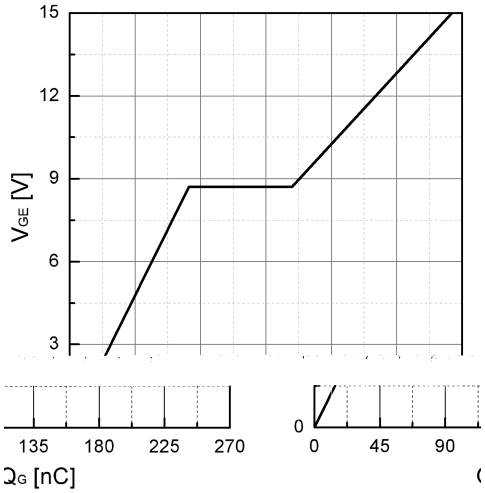


Fig 4. Typical Gate charge

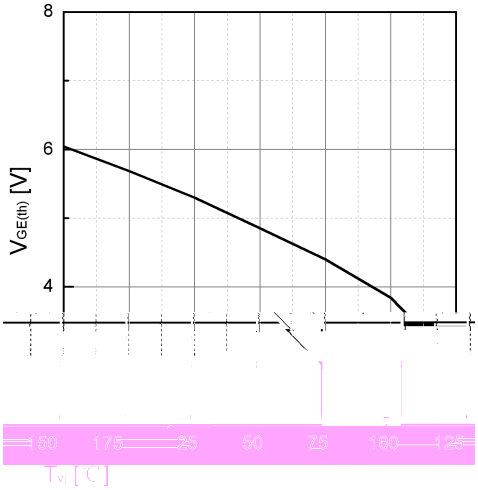


Fig 5. Typical $V_{GE(th)}$ as a function of T_{vj} (I_C=1mA)

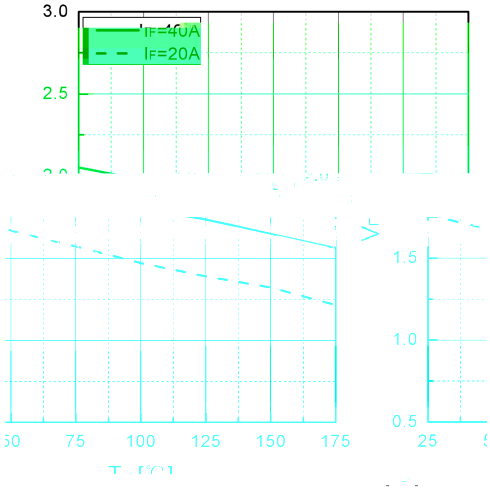


Fig 6. Typical V_F as a function of T_{vj}

Typical performance characteristics

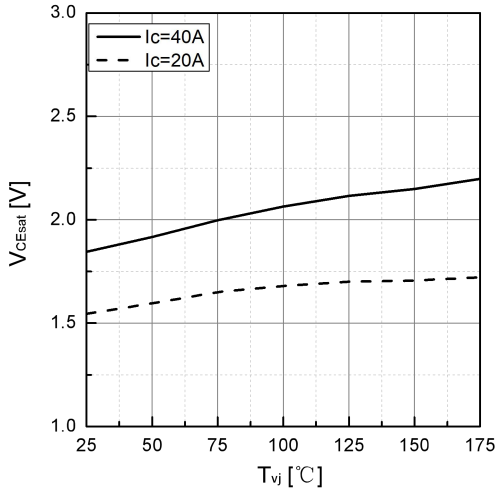


Fig 7. Typical V_{CEsat} as a function of T_{vj}

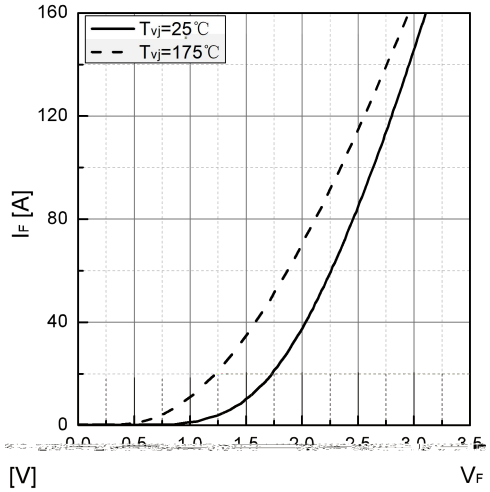


Fig 8. Typical I_F as a function of V_F

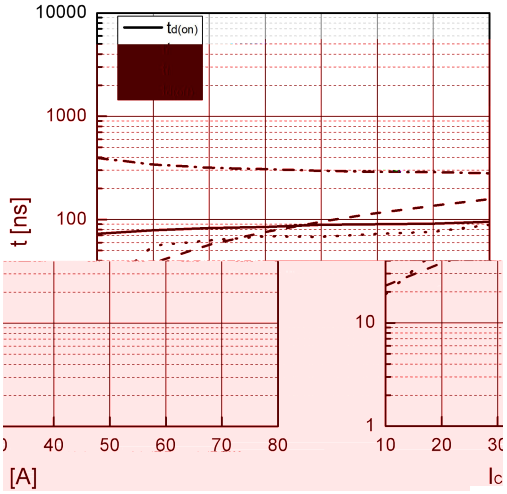


Fig 9. Typical switching time as a function of I_C

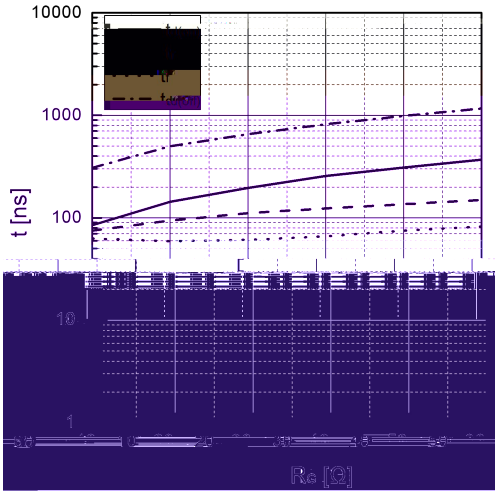


Fig 10. Typical switching times as a function of R_G

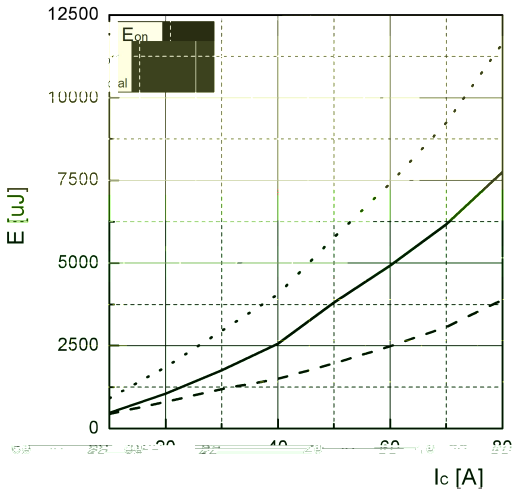


Fig 11. Typical switching energy losses as a function of I_C

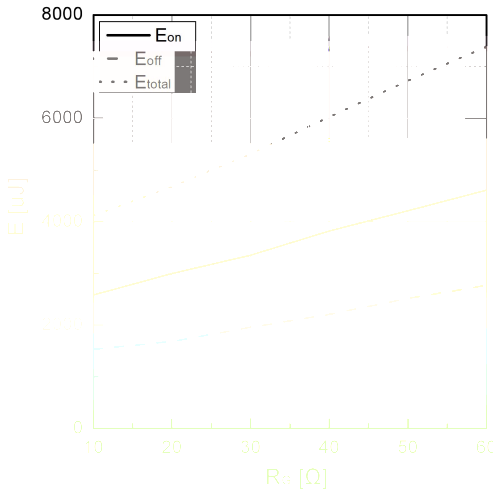


Fig 12. Typical switching energy losses as a function of R_G

Typical performance characteristics

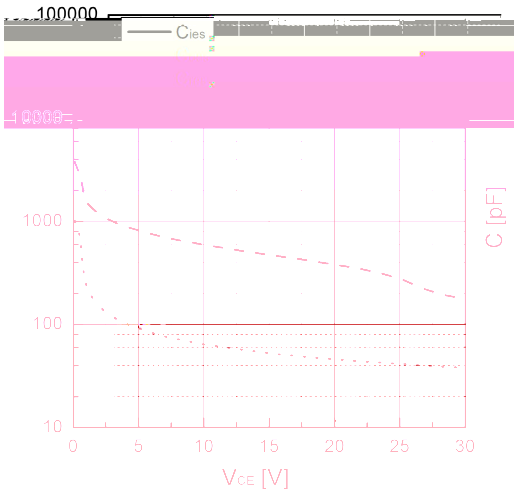


Fig 13. Typical capacitance as a function of V_{CE} (f=1Mhz, V_{GE}=0V)

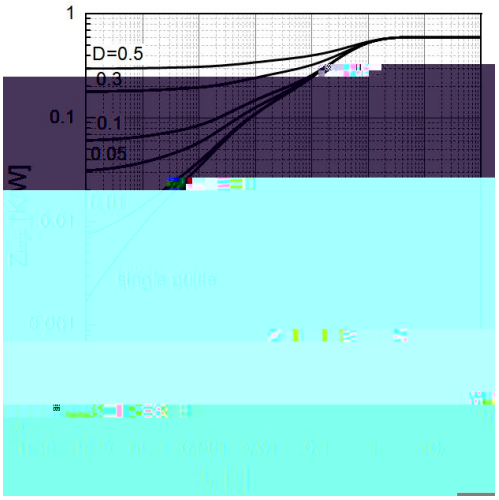


Fig 14. Transient thermal impedance of IGBT

Package dimension

TO-247i

				Inches		
					Typ.	Max.
					0.622	0.634
					0.827	0.835
					0.787	0.799
					0.079	0.087
					0.083	0.091
					0.047	0.055
G					-	0.222
H	4.80	5.00	5.20	9	0.197	0.205
J	1.90	2.00	2.10	0.075	0.079	0.083
K	2.20	2.35	2.50	0.087	0.093	0.098
L	0.41	0.60	0.79	0.016	0.024	0.031
M	2.80	3.00	3.20	0.110	0.118	0.126
N	2.90	3.10	3.30	0.114	0.122	0.130

Date	Revision	Changes
2025-12-17	Rev. 1.0	Release